

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

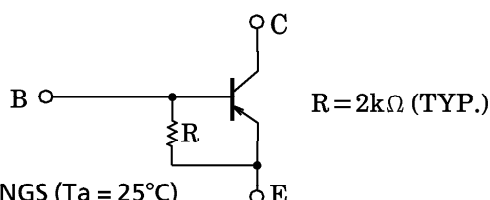
# RN6001

MOTOR DRIVE CIRCUIT APPLICATIONS.

POWER AMPLIFIER APPLICATIONS.

POWER SWITCHING APPLICATIONS.

- With Built-in Bias Resistors
  - Simplify Circuit Design
  - Reduce a Quantity of Parts and Manufacturing Process
  - Small Flat Package
  - $P_C = 1 \sim 2W$  (Mounted on Ceramic substrate)
  - Complementary to RN5001
- EQUIVALENT CIRCUIT

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-30	V
Collector-Emitter Voltage	$V_{CES}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-2	A
Base Current	$I_B$	-0.4	A
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation	$P_C^*$	1000	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ\text{C}$

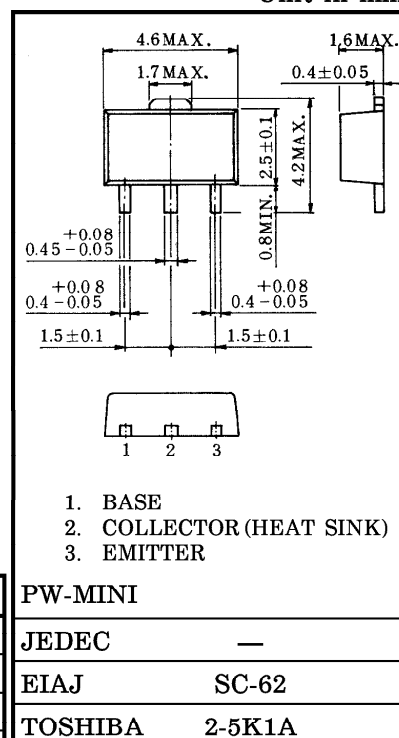
\* : Mounted on ceramic substrate ( $250\text{mm}^2 \times 0.8\text{t}$ )ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -30V, I_E = 0$	—	—	-0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-1.92	-2.5	-3.57	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = -1\text{mA}$	-30	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -0.5A$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -2.0A$	50	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -0.05A$	—	—	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1A, I_C = -0.05A$	—	—	-1.2	V
Transition Frequency	$f_T$	$V_{CE} = -2V, I_C = -0.5A$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1\text{MHz}$	—	40	—	pF
Resistor	R		1.4	2.0	2.6	k $\Omega$

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Unit in mm



Weight : 0.05g

MARKING

